

Title (en)

A METHOD FOR LASER TREATMENT OF IMPLANTABLE DEVICES, IMPLANTABLE DEVICES OBTAINED USING SAID METHOD, AND A LASER SYSTEM FOR TREATMENT OF IMPLANTABLE DEVICES

Title (de)

VERFAHREN ZUR LASERBEHANDLUNG VON IMPLANTIERBAREN VORRICHTUNGEN, MIT DIESEM VERFAHREN ERHALTENE IMPLANTIERBARE VORRICHTUNGEN UND LASERSYSTEM ZUR BEHANDLUNG VON IMPLANTIERBAREN VORRICHTUNGEN

Title (fr)

PROCEDE POUR LE TRAITEMENT AU LASER DE DISPOSITIFS IMPLANTABLES, DISPOSITIFS IMPLANTABLES OBTENUS EN UTILISANT LEDIT PROCEDE ET SYSTEME LASER POUR LE TRAITEMENT DE DISPOSITIFS IMPLANTABLES

Publication

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Application

EP 07705559 A 20070208

Priority

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- IT TO20060089 A 20060208

Abstract (en)

[origin: WO2007091155A1] Method for the laser treatment of implantable devices comprising the step of treating a surface of the implantable device (1) via a diode-pumped solid-state laser (DPSS) in Q-switch regime for creating on the device itself a surface morphology comprising a controlled distribution of pores (5) having a diameter and depth of between 3 and 150 µm and preferably 5-20 µm, and a pitch of between 5 and 300 µm and preferably between 10 and 30 µm.

IPC 8 full level

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CPC (source: EP)

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Citation (search report)

See references of WO 2007091155A1

Citation (examination)

US 6419491 B1 20020716 - RICCI JOHN [US], et al

Cited by

GB2476969A; WO2011086529A1

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